

ABSTRACT

Provided is a silver alloy sputtering target for forming an electroconductive film, the sputtering target being capable of inhibiting splashing even when a large electric power is applied to the target in line with increased target size, having excellent corrosion resistance and heat resistance, and being capable of forming a low-electrical-resistance film. Also provided is a method for manufacturing such a sputtering target. This silver alloy sputtering target for forming an electroconductive film comprises a silver alloy having a component composition containing a total of 0.1 to 1.5% by mass of Ga and/or Sn and the balance composed of Ag and unavoidable impurities; or comprises a silver alloy having a component composition further containing 0.1 to 1.5% by mass of In. The average grain diameter of the crystal grains of the silver alloy is 120 to 400 μm , or 120 to 250 μm when In is included. The dispersion in the grain diameter of the crystal grains is 20% or less of the average grain diameter.

[Selected Figure] FIG. 1